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Dual 4-bit Decade Counters

RENESAS

ADE-205-507 (Z) 1st. Edition Sep. 2000

Description

This circuit contains eight master-slave flip-flops and additional gating to implement two individual 4-bit decade counters. Each decade counter has individual clock, clear and set-to-9 inputs. BCD count sequences of any length up to divide-by-100 may be implemented with a single HD74HC490. Buffering on each output is provided to ensure that suceptibility to collector communication is reduced significantly. The counters have paralle outputs from each counter state so that submultiples of the input count frequency are available for system timing signals.

Features

- High Speed Operation: t_{pd} (Clock to Q_A) = 13 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

Function Table

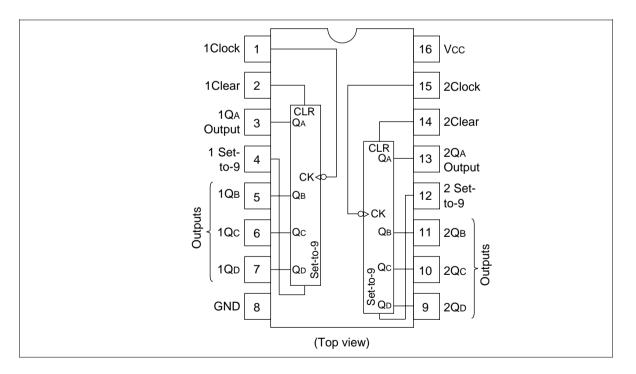
Clear/Set-To-9

Inputs		Outputs						
Clear	Set-To-9	Q _A	Q _B	Q _c	\mathbf{Q}_{D}			
Н	L	L	L	L	L			
L	Н	н	L	L	Н			
L	L	Count						

BCD Count Sequence

	Outputs				
Count	Q _D	Q _c	Q _B	Q _A	
0	L	L	L	L	
1	L	L	L	Н	
2	L	L	Н	L	
3	L	L	Н	Н	
4	L	Н	L	L	
5	L	Н	L	Н	
6	L	Н	Н	L	
7	L	Н	Н	Н	
8	Н	L	L	L	
9	Н	L	L	Н	

Pin Arrangement



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DC Characteristics

			Ta =	: 25°C		Ta = - +85°C	–40 to C			
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Condition	าร
Input voltage	V _{IH}	2.0	1.5			1.5	_	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2		—	4.2	—	_		
	V _{IL}	2.0			0.5	—	0.5	V		
		4.5		_	1.35	_	1.35	_		
		6.0	_	_	1.8	_	1.8	_		
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	$Vin = V_{IH} \text{ or } V_{IL}$	I _{OH} = -20 μA
		4.5	4.4	4.5	_	4.4	_	_		
		6.0	5.9	6.0	—	5.9	—	_		
		4.5	4.18			4.13	—	_		$I_{OH} = -4 \text{ mA}$
		6.0	5.68		_	5.63	_	_		I _{он} = -5.2 mA
	V _{OL}	2.0		0.0	0.1	—	0.1	V	$Vin = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20 \ \mu A$
		4.5		0.0	0.1	—	0.1	_		
		6.0	_	0.0	0.1	_	0.1	_		
		4.5			0.26		0.33	_		$I_{OL} = 4 \text{ mA}$
		6.0			0.26		0.33	_		I _{oL} = 5.2 mA
Input current	lin	6.0	_	_	±0.1	_	±1.0	μΑ	$Vin = V_{CC} \text{ or } GN$	ND
Quiescent supply current	I _{cc}	6.0		—	4.0	—	40	μΑ	Vin = V _{cc} or GN	ND, lout = 0 μA

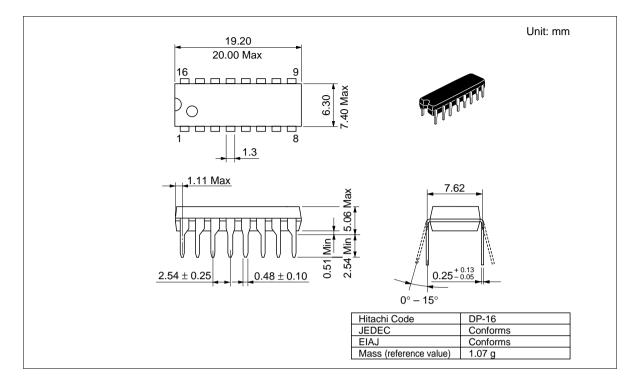


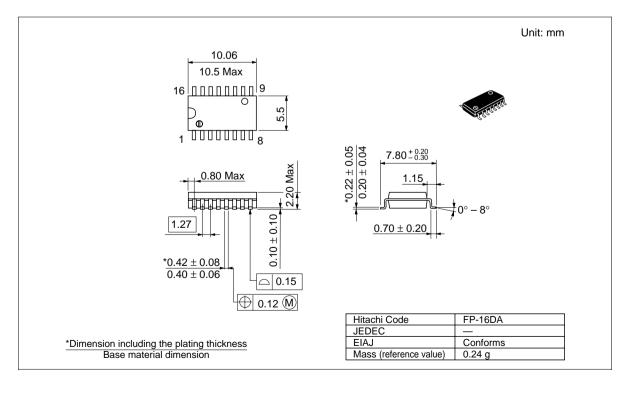
AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

			Ta =	: 25°C	;	Ta = · +85°0	–40 to C		
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Maximum clock	f_{max}	2.0	_	_	4	_	3	MHz	
frequency		4.5	_	_	20	_	16	_	
		6.0		_	24	—	19	_	
Propagation delay	t _{PLH}	2.0		_	120	—	150	ns	Clock to Q _A
time	t _{PHL}	4.5	_	13	24	—	30	_	
		6.0		—	20	—	26	_	
	t _{PLH}	2.0		—	205	—	255	ns	Clock to Q _B Q _C
	t _{PHL}	4.5		21	41	—	51	_	
		6.0		—	35	—	43	_	
	t _{PLH}	2.0		—	280	—	350	ns	Clock to Q _c
	t _{PHL}	4.5	_	23	56	—	70	_	
		6.0		—	48	—	60	_	
	t _{PHL}	2.0		—	205	_	255	ns	Clear to any output
		4.5		18	41		51	_	
	_	6.0	—	—	35	—	43		
	t _{PLH}	2.0		—	205	_	255	ns	Set-to-9 to Q_A , Q_D
		4.5		13	41		51	_	
	_	6.0		_	35		43		
	t _{PHL}	2.0	—	—	190		240	ns	Set-to-9 to $Q_{\rm B}$, $Q_{\rm C}$
		4.5	—	17	38		48	_	
		6.0		_	32		41		
Pulse width	t _w	2.0	80	—	—	100	_	ns	
		4.5	16	6		20	_	_	
		6.0	14	_		17	_		
Setup time	t _{su}	2.0	100	—	—	125		ns	
		4.5	20	1	—	25		_	
		6.0	17	_		21	_		
Output rise/fall	t _{TLH}	2.0	_	_	75		95	ns	
time	t_{THL}	4.5	_	5	15	—	19	_	
		6.0	_	_	13	_	16		
Input capacitance	Cin	_	_	5	10	_	10	pF	

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Package Dimensions





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